

# Silicon Carbide (SiC) Schottky Diode – EliteSiC, 10 A, 650 V, D2, DPAK

# FFSD1065B-F085

# **Description**

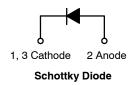
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### **Features**

- Max Junction Temperature 175°C
- Avalanche Rated 49 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

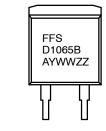
# **Applications**

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters





#### **MARKING DIAGRAM**



FFSD1065B = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
ZZ = Assembly Lot Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

# FFSD1065B-F085

# ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		49	mJ
I <sub>F</sub>	Continuous Rectified Forward Current @ T <sub>C</sub> < 150°C		10	Α
	Continuous Rectified Forward Current @ T <sub>C</sub> < 135°C		13.5	
I <sub>F, Max</sub>	Non-Repetitive Peak Forward Surge Current	T <sub>C</sub> = 25°C, 10 μs	650	Α
		T <sub>C</sub> = 150°C, 10 μs	570	Α
I <sub>F,SM</sub>	Non-Repetitive Forward Surge Current $T_C = 25^{\circ}C$	Half-Sine Pulse, t <sub>p</sub> = 8.3 ms	45	Α
Ptot	Power Dissipation	T <sub>C</sub> = 25°C	98	W
		T <sub>C</sub> = 150°C	16	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		−55 to +175	°C
	TO-247 Mounting Torque, M3 Screw		60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $E_{AS}$  of 49 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 14$  A, V = 50 V.

# THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max	1.53	°C/W

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 10 A, T <sub>C</sub> = 25°C	-	1.38	1.7	V
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 125°C	-	1.6	2.0	
		I <sub>F</sub> = 10 A, T <sub>C</sub> = 175°C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 650 V, T <sub>C</sub> = 25°C	-	0.5	40	μΑ
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 125°C	-	1	80	
		V <sub>R</sub> = 650 V, T <sub>C</sub> = 175°C	-	2	160	
Q <sub>C</sub>	Total Capacitive Charge	V = 400 V	-	25	-	nC
С	Total Capacitance	V <sub>R</sub> = 1 V, f = 100 kHz	-	424	-	pF
		V <sub>R</sub> = 300 V, f = 100 kHz	-	39	-	
		V <sub>R</sub> = 600 V, f = 100 kHz	_	35	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **ORDERING INFORMATION**

Part Number	Top Marking	Package	Shipping*
FFSD1065B-F085	FFSD1065B	DPAK (Pb-Free / Halogen Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

# FFSD1065B-F085

# **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)

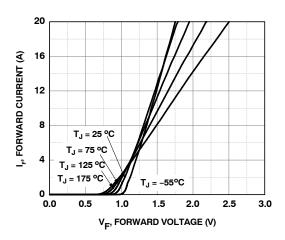


Figure 1. Forward Characteristics

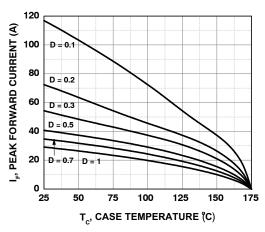


Figure 3. Current Derating

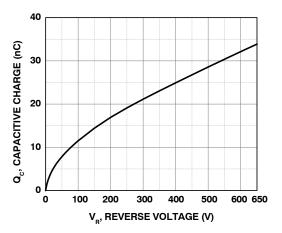


Figure 5. Capacitive Charge vs. Reverse Voltage

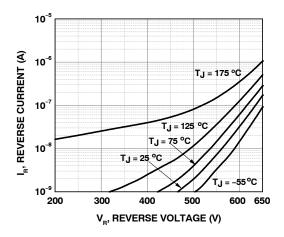


Figure 2. Reverse Characteristics

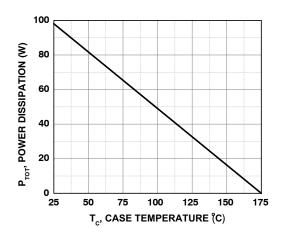


Figure 4. Power Derating

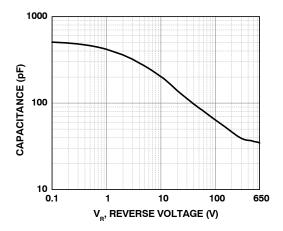


Figure 6. Capacitance vs. Reverse Voltage

# FFSD1065B-F085

# TYPICAL CHARACTERISTICS (CONTINUED)

(T<sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)

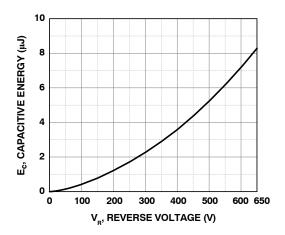


Figure 7. Capacitance Stored Energy

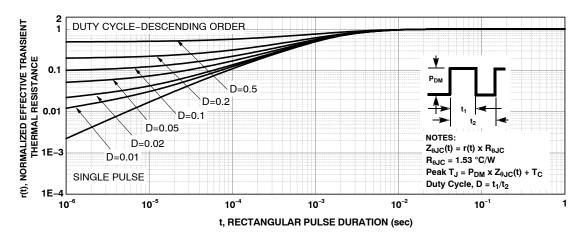


Figure 8. Junction-to-Case Transient Thermal Response Curve

# **TEST CIRCUIT AND WAVEFORMS**

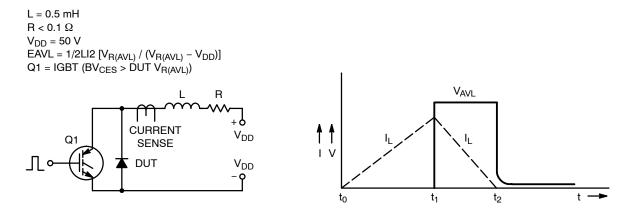


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform





# DPAK3 6.10x6.54x2.29, 4.57P CASE 369AS **ISSUE B**

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**DATE 20 DEC 2023** 

- NOTES: UNLESS OTHERWISE SPECIFIED

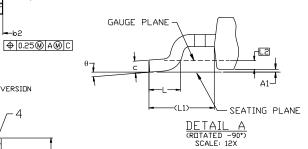
  A) THIS PACKAGE CONFORMS TO JEDEC, TO-252, ISSUE F, VARIATION AA.

  B) ALL DIMENSIONS ARE IN MILLIMETERS.

  C) DIMENSIONING AND TOLERANCING PER

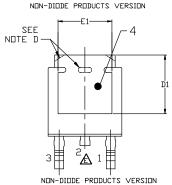
A

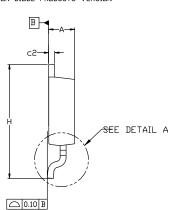
- F)
- DIMENSIONING AND TOLERANCING PER
  ASME Y14.5M-2018.
  SUPPLIER DEPENDENT MOLD LOCKING HOLES OR CHAMFERED
  CORNERS OR EDGE PROTRUSION.
  FOR DIGDE PRODUCTS, L4 IS 0.25 MM MAX PLASTIC BODY
  STUB WITHOUT CENTER LEAD.
  DIMENSIONS ARE EXCLUSIVE OF BURRS,
  MOLD FLASH AND TIE BAR EXTRUSIONS.
  LAND PATTERN RECOMMENDATION IS BASED ON IPC7351A STD
  T0228P991X239-3N.



MILLIME LEKS				
MIN.	N□M.	MAX.		
2.18	2.29	2.39		
0.00	-	0.127		
0.64	0.77	0.89		
0.76	0.95	1.14		
5.21	5.34	5.46		
0.45	0.53	0.61		
0.45	0.52	0.58		
5.97	6.10	6.22		
5.21				
6.35	6.54	6.73		
4.32				
2.286 BSC				
4.572 BSC				
9.40	9.91	10.41		
1.40	1.59	1.78		
2.90 REF				
0.51 BSC				
0.89	1.08	1.27		
		1.02		
0*		10°		
	MIN. 2.18 0.00 0.64 0.76 5.21 0.45 0.45 5.97 5.21 6.35 4.32 2.6 4.5 9.40 1.40	MIN. N□M. 2.18 2.29 0.00 - 0.64 0.77 0.76 0.95 5.21 5.34 0.45 0.52 5.97 6.10 5.21 6.35 6.54 4.32 2.≥88 BS 4.57≥ BS 9.40 9.91 1.40 1.59 2.90 RE 0.51 BS		

MILL IMETERS





-5.55	MIN-
6.40	6.50 MIN
	2.85 MIN
4.5	1.25 MIN 2.286

#### LAND PATTERN RECOMMENDATION

\*FOR ADDITIONAL INFORMATION ON DUR
PB-FREE STRATEGY AND SOLDERING DETAILS,
PLEASE DOWNLOAD THE ON SEMICONDUCTOR
SOLDERING AND MOUNTING TECHNIQUES
REFERENCE MANUAL, SOLDERRM/D.

# **GENERIC MARKING DIAGRAM\***

XXXXXX XXXXXX **AYWWZZ** 

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "=", may or may not be present. Some products may not follow the Generic Marking.

XXXX = Specific Device Code

= Assembly Location Α

Υ = Year

WW = Work Week

77 = Assembly Lot Code

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